TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER GaAs FET TIM6472-16EL

FEATURES

HIGH POWER

P1dB=42.5dBm at 6.4GHz to 7.2GHz

■ HIGH GAIN G1dB= 11.0dB at 6.4GHz to 7.2GHz BROAD BAND INTERNALLY MATCHED FET

■ HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS ($Ta= 25 \circ C$)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain	P1dB		dBm	41.5	42.5	
Compression Point						
Power Gain at 1dB Gain	G1dB	VDS= 10V	dB	10.0	11.0	
Compression Point		IDSset=2.8A				
Drain Current	IDS1	f = 6.4 to 7.2GHz	А		4.4	5.0
Gain Flatness	ΔG		dB			±0.8
Power Added Efficiency	ηadd		%		37	
3rd Order Intermodulation	IM3	Two-Tone Test	dBc	-40	-45	
Distortion		Po= 30.5dBm				
Drain Current	IDS2	(Single Carrier Level)	А		4.4	5.0
Channel Temperature Rise	∆Tch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C			80

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 5.2A	S	—	5.2	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 40mA	V	-1.0	-1.9	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A		8.8	—
Gate-Source Breakdown Voltage	VGSO	IGS= -180μA	V	-5		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.5	1.8

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TOSHIBA CORPORATION

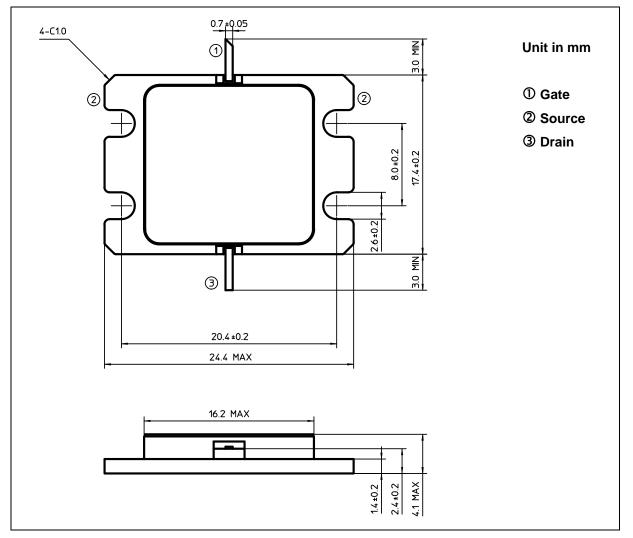
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TIM6472-16EL

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	14
Total Power Dissipation (Tc= 25 $^{\circ}\text{C}$)	PT	W	83.3
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA05A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.